

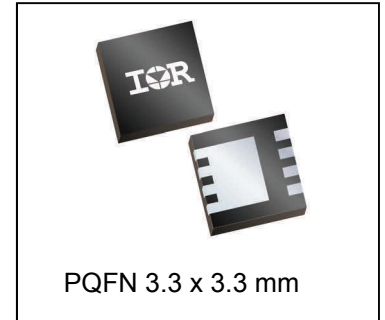
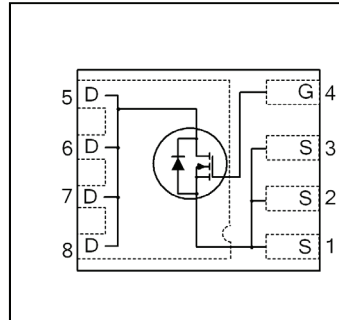


**THE DATASHEET OF  
IRFHM4226TRPBF**



HEXFET® Power MOSFET

<b>V<sub>DSS</sub></b>	<b>25</b>	<b>V</b>
<b>R<sub>DS(on)</sub> max</b> (@ V <sub>GS</sub> = 10V)	<b>2.4</b>	<b>mΩ</b>
(@ V <sub>GS</sub> = 4.5V)	<b>3.3</b>	
<b>Qg (typical)</b>	<b>16</b>	<b>nC</b>
<b>I<sub>D</sub></b> (@T <sub>C (Bottom)</sub> = 25°C)	<b>60</b> Ⓣ	<b>A</b>



### Applications

- Control or Synchronous MOSFET for high frequency buck converters

### Features

Low R <sub>DS(on)</sub> (<2.4mΩ)
Low Charge (typical 16nC)
Low Thermal Resistance to PCB (<3.2°C/W)
Low Profile (<0.9 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1

results in

⇒

### Benefits

Lower Conduction Losses
Low Switching Losses
Enable better thermal dissipation
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFHM4226TRPbF	PQFN 3.3mm x 3.3mm	Tape and Reel	4000	IRFHM4226TRPbF

### Absolute Maximum Ratings

	Parameter	Max.	Units
V <sub>GS</sub>	Gate-to-Source Voltage	± 20	V
I <sub>D</sub> @ T <sub>A</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	28	A
I <sub>D</sub> @ T <sub>C(Bottom)</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	105Ⓣ	
I <sub>D</sub> @ T <sub>C(Bottom)</sub> = 100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V	67Ⓣ	
I <sub>D</sub> @ T <sub>C</sub> = 25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V (Source Bonding Technology Limited)	60Ⓣ	
I <sub>DM</sub>	Pulsed Drain Current ①	420Ⓢ	
P <sub>D</sub> @ T <sub>A</sub> = 25°C	Power Dissipation ⑤	2.7	W
P <sub>D</sub> @ T <sub>C(Bottom)</sub> = 25°C	Power Dissipation ⑤	39	
	Linear Derating Factor ⑤	0.021	W/°C
T <sub>J</sub> T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑤ are on page 9

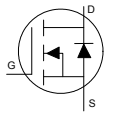
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	25	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	21	—	mV/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	1.7	2.4	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A ③
		—	2.6	3.3		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 30A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	1.1	1.6	2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50μA
ΔV <sub>GS(th)</sub>	Gate Threshold Voltage Coefficient	—	-5.7	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1.0	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	136	—	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 30A
Q <sub>g</sub>	Total Gate Charge	—	32	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 13V, I <sub>D</sub> = 30A
Q <sub>g</sub>	Total Gate Charge	—	16	24	nC	V <sub>DS</sub> = 13V V <sub>GS</sub> = 4.5V I <sub>D</sub> = 30A
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	—	3.6	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	2.0	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	5.8	—		
Q <sub>godr</sub>	Gate Charge Overdrive	—	4.6	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	7.8	—		
Q <sub>oss</sub>	Output Charge	—	15	—	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	—	1.1	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	11	—	ns	V <sub>DD</sub> = 13V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 30A R <sub>G</sub> = 1.8Ω
t <sub>r</sub>	Rise Time	—	35	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	14	—		
t <sub>f</sub>	Fall Time	—	8.1	—		
C <sub>iss</sub>	Input Capacitance	—	2000	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 13V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	570	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	150	—		

**Avalanche Characteristics**

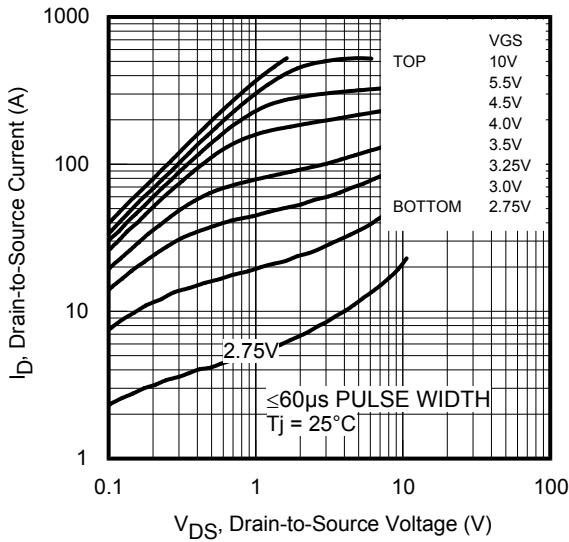
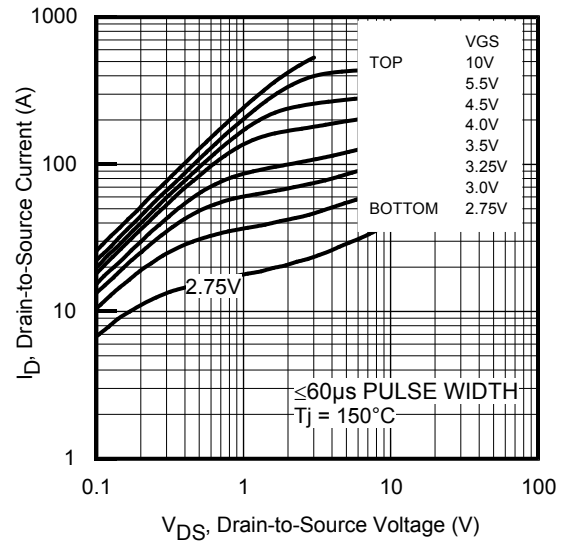
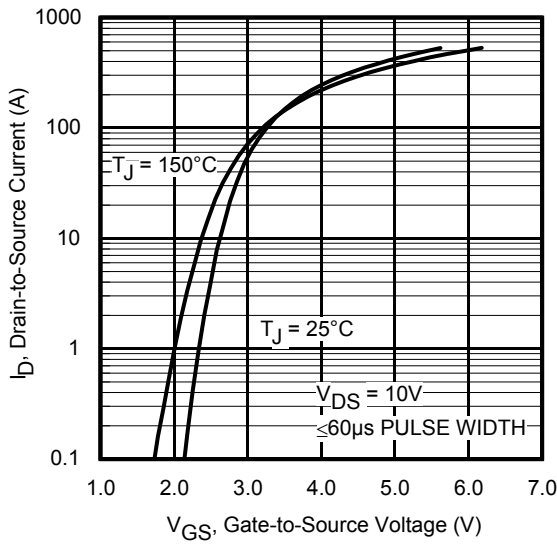
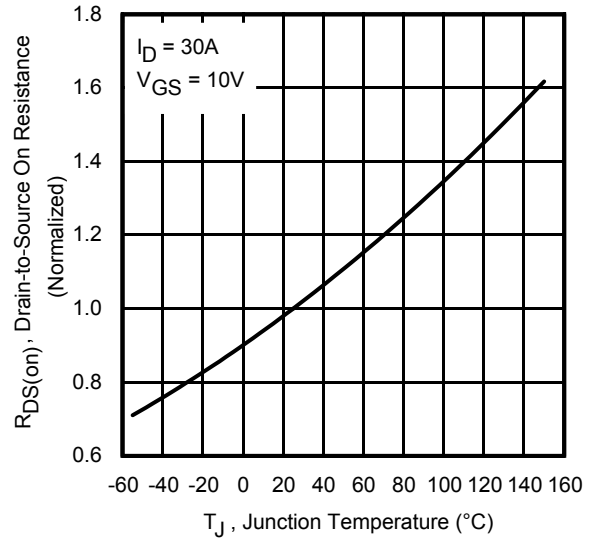
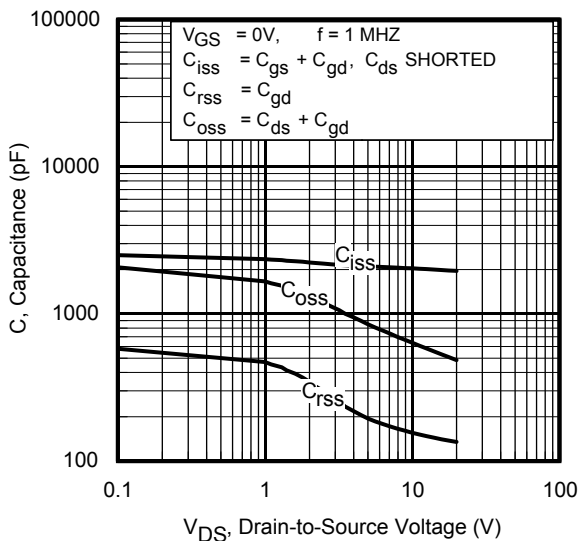
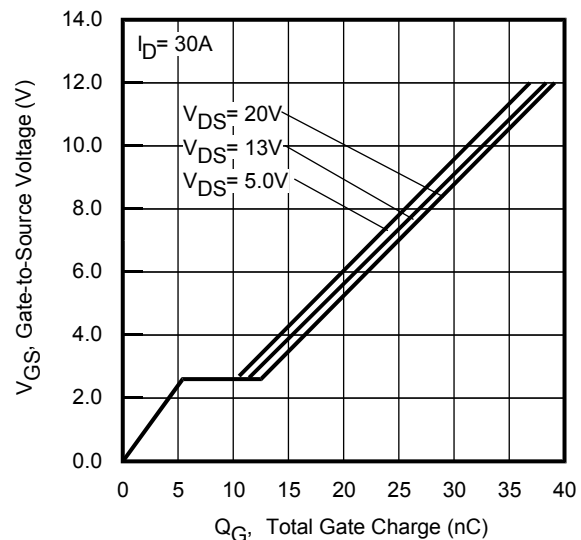
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	124	mJ
I <sub>AR</sub>	Avalanche Current ①	—	30	A

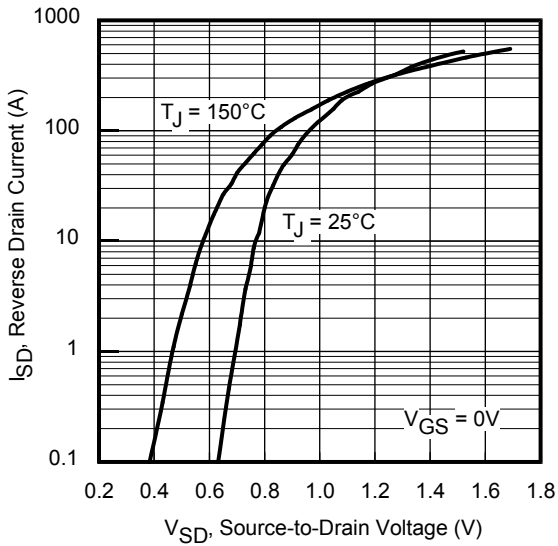
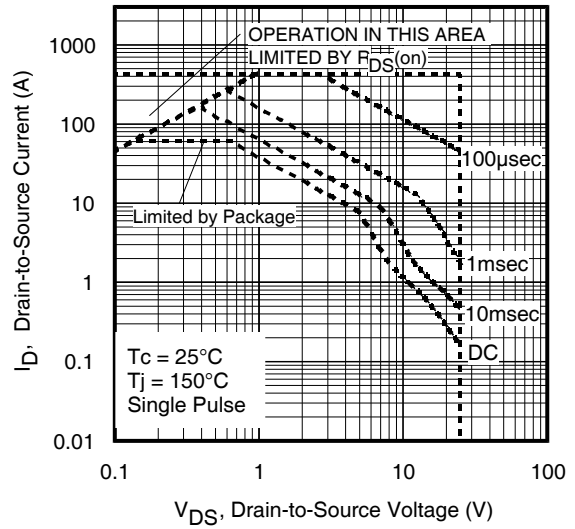
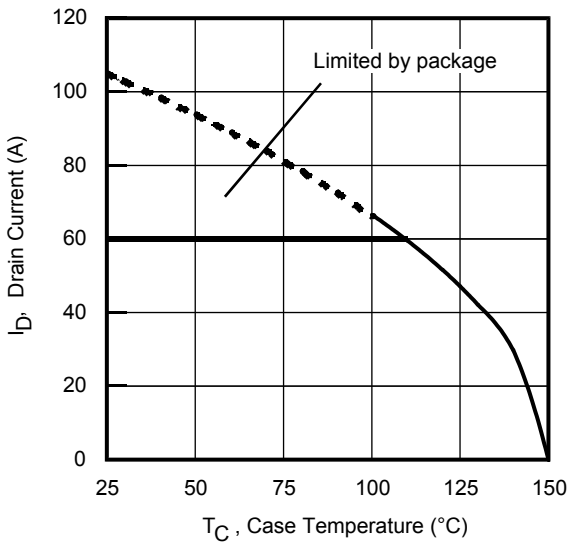
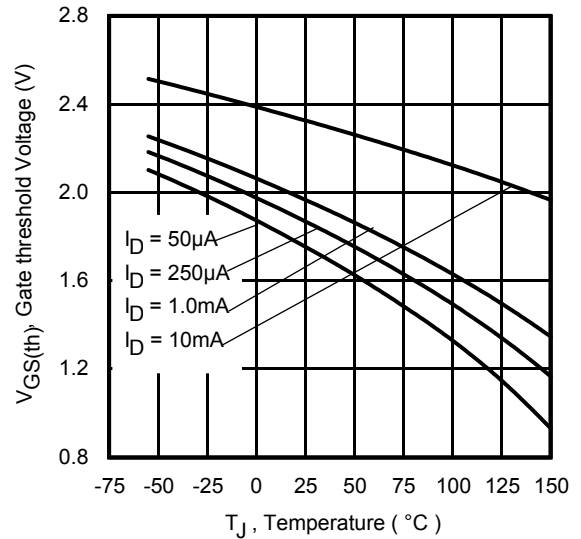
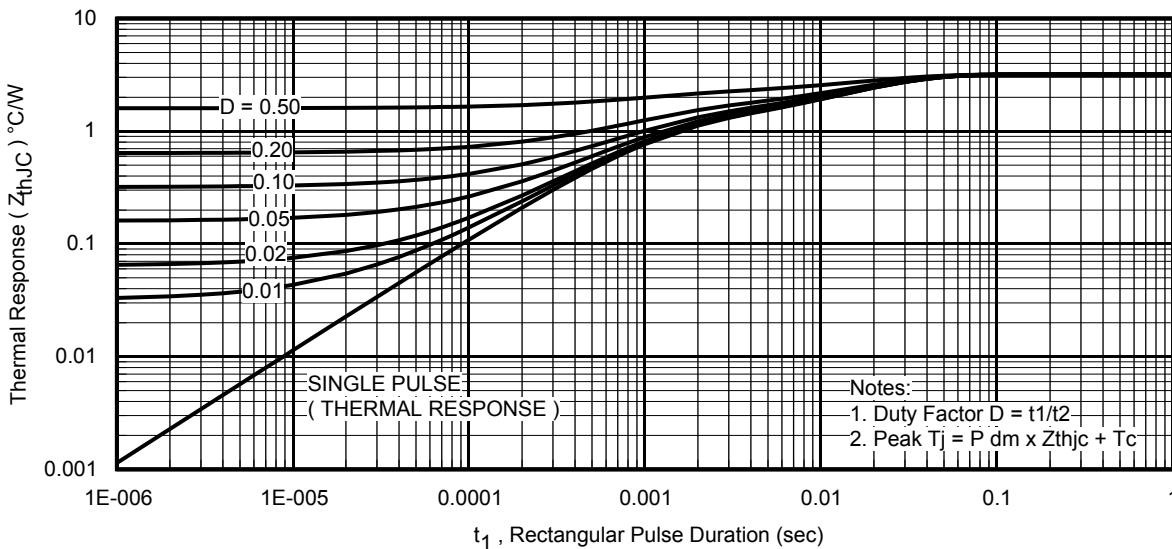
**Diode Characteristics**

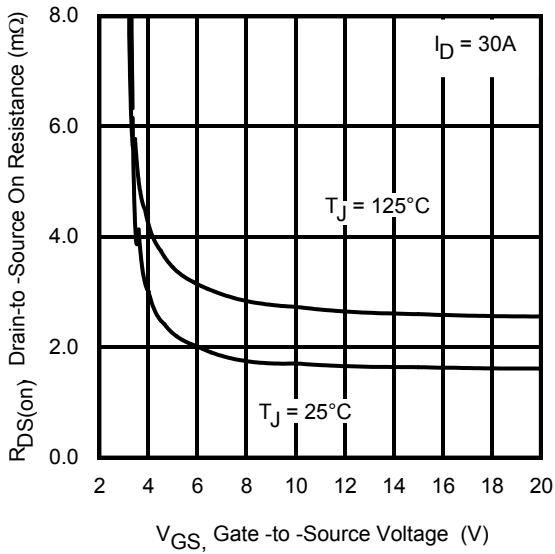
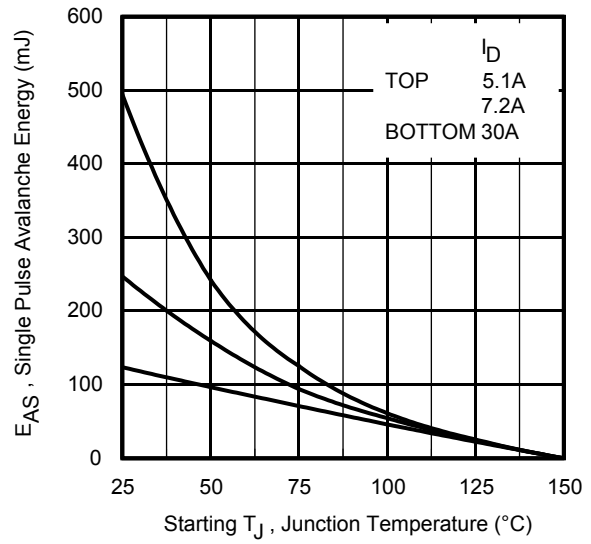
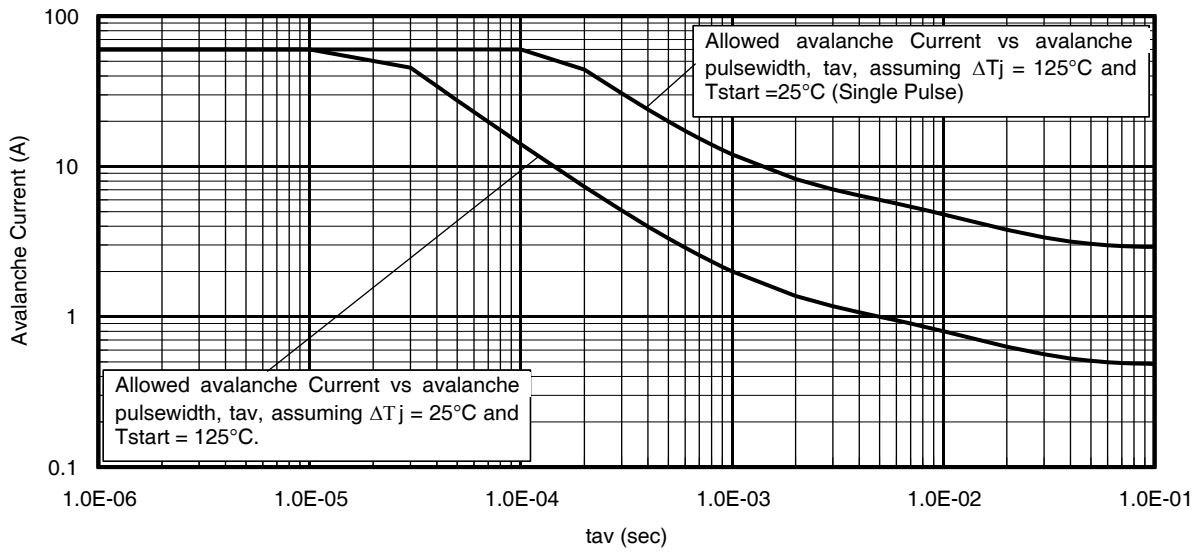
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	60⑥⑦	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	420⑧		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 30A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	16	24	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 30A, V <sub>DD</sub> = 13V
Q <sub>rr</sub>	Reverse Recovery Charge	—	28	42	nC	di/dt = 450A/μs ③

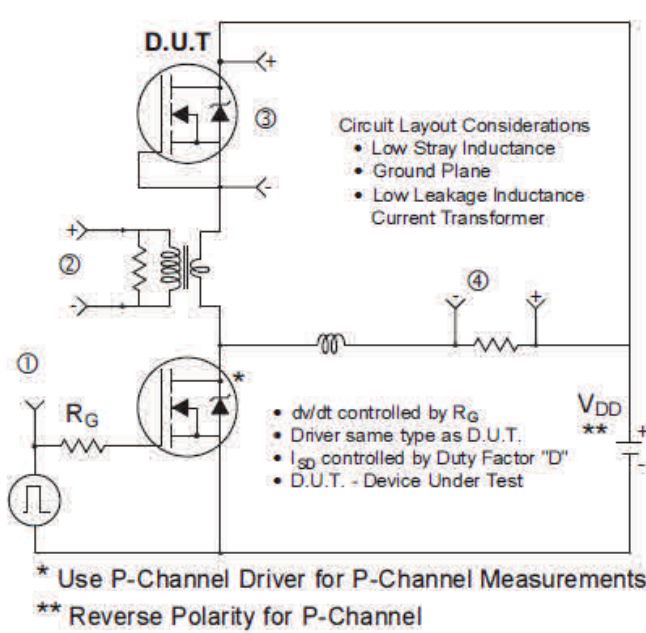
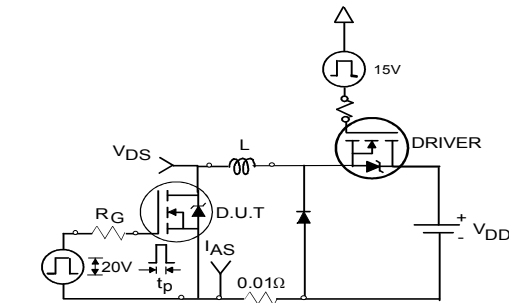
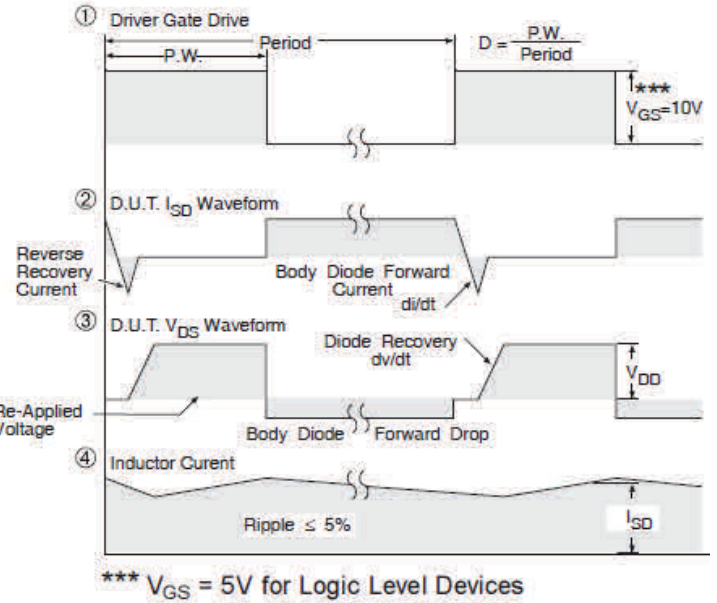
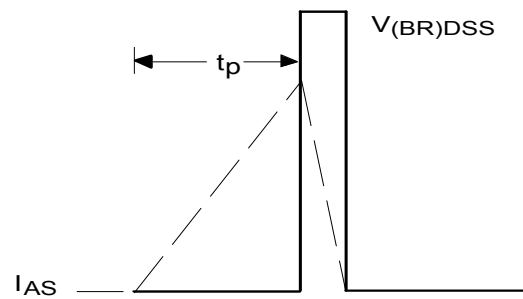
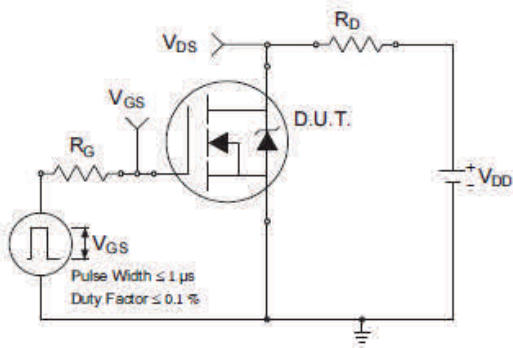
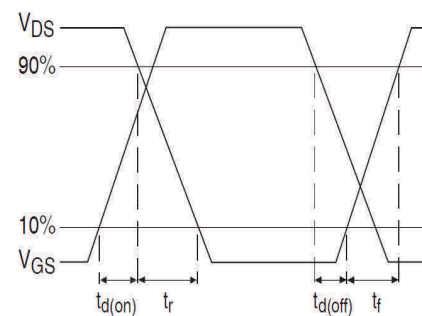
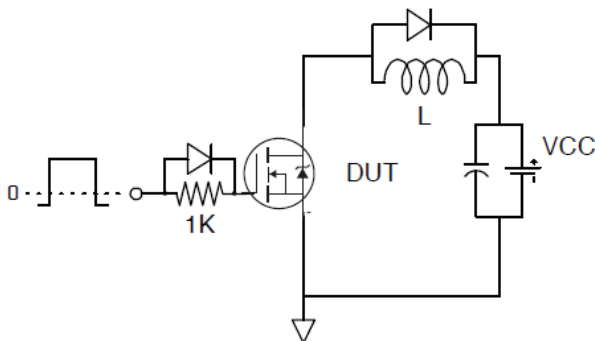
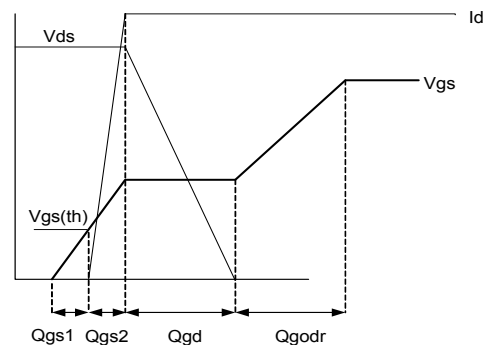
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC</sub> (Bottom)	Junction-to-Case ④	—	3.2	°C/W
R <sub>θJC</sub> (Top)	Junction-to-Case ④	—	35	
R <sub>θJA</sub>	Junction-to-Ambient ⑤	—	47	
R <sub>θJA</sub> (<10s)	Junction-to-Ambient ⑤	—	30	

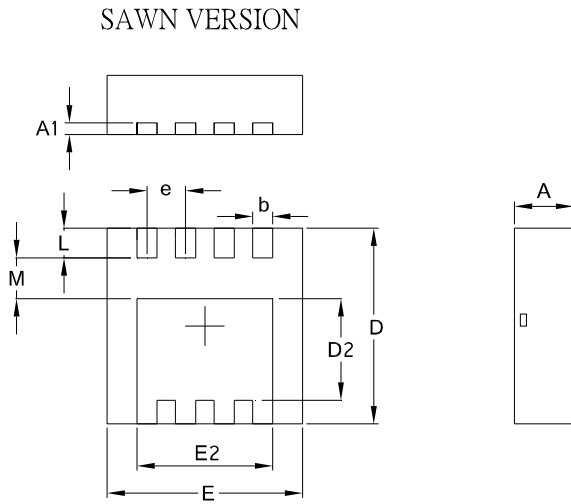

**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance vs. Temperature**

**Fig 5. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage**


**Fig 7.** Typical Source-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area

**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10.** Threshold Voltage Vs. Temperature

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case


**Fig 12.** On-Resistance vs. Gate Voltage

**Fig 13.** Maximum Avalanche Energy vs. Drain Current

**Fig 14.** Single Avalanche Current vs. pulse Width


**Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**

**Fig 16a. Unclamped Inductive Test Circuit**

**Fig 16b. Unclamped Inductive Waveforms**

**Fig 17a. Switching Time Test Circuit**

**Fig 17b. Switching Time Waveforms**

**Fig 18. Gate Charge Test Circuit**

**Fig 19. Gate Charge Waveform**

## PQFN 3.3 x 3.3 Outline “B” Package Details

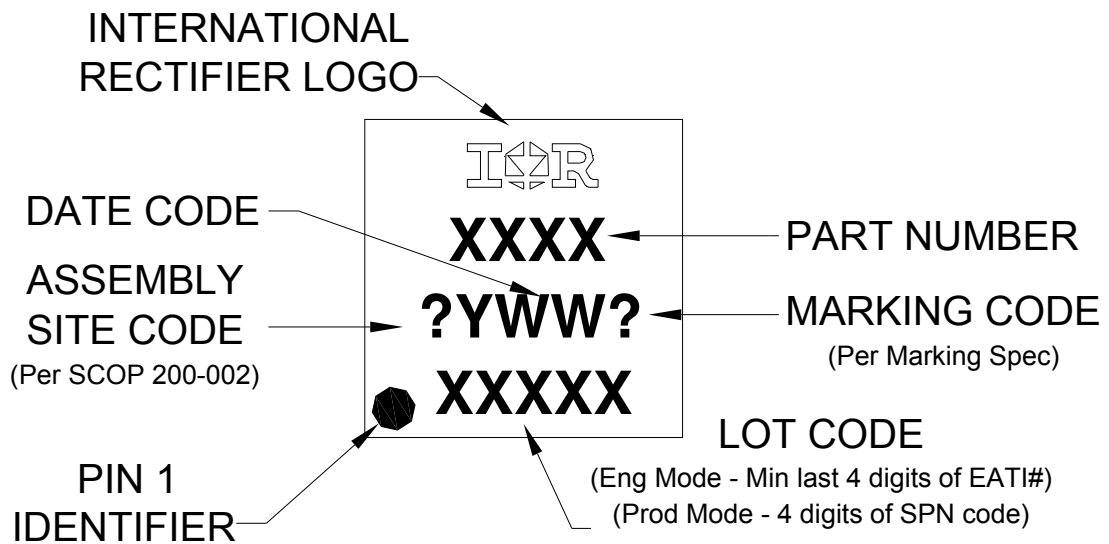


SYMBOL	COMMON			
	MM		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.05	0.0276	0.0413
A1	0.12	0.39	0.0047	0.0154
b	0.25	0.39	0.0098	0.0154
D	3.20	3.45	0.1260	0.1358
D1	3.00	3.20	0.1181	0.1417
D2	1.69	2.20	0.0665	0.0866
E	3.20	3.40	0.1260	0.1339
E1	3.00	3.20	0.1181	0.1417
E2	2.15	2.59	0.0846	0.1020
e	0.65 BSC		0.0256 BSC	
L	0.15	0.55	0.0059	0.0217
M	0.59	—	0.0232	—
O	9Deg	12Deg	9Deg	12Deg

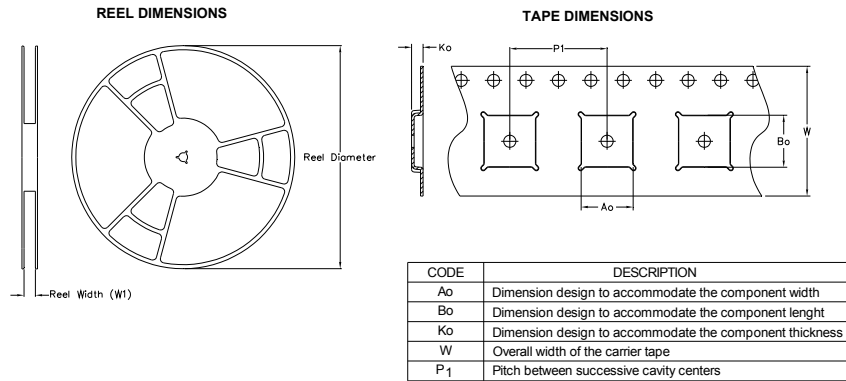
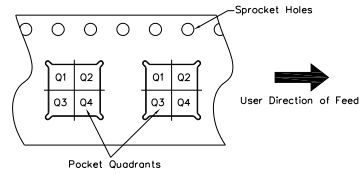
For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136: <http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154: <http://www.irf.com/technical-info/appnotes/an-1154.pdf>

### PQFN 3.3 x 3.3 Part Marking



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**PQFN 3.3 x 3.3 Tape and Reel**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
3.3 X 3.3 PQFN	13	4000	12.4	3.600	3.600	1.20	8.00	12	Q1

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**Qualification Information†**

<b>Moisture Sensitivity Level</b>	PQFN 3.3mm x 3.3mm	MSL1 (per JEDEC J-STD-020D††)
<b>RoHS Compliant</b>	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

†† Applicable version of JEDEC standard at the time of product release.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.275\text{mH}$ ,  $R_G = 50\Omega$ ,  $I_{AS} = 30\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .
- ⑤ When mounted on 1 inch square PCB (FR-4). Please refer to AN-994 for more details:  
<http://www.irf.com/technical-info/appnotes/an-994.pdf>
- ⑥ Calculated continuous current based on maximum allowable junction temperature.
- ⑦ Current is limited to 60A by source bonding technology.
- ⑧ Pulse drain current is limited at 240A by source bonding technology.

**Revision History**

Date	Comments
08/07/2013	<ul style="list-style-type: none"> <li>• Added "Fast/RFET™" above part number, on page 1</li> </ul>
12/5/2013	<ul style="list-style-type: none"> <li>• Updated fig. 14, limit curve to 40A package limitation current, on page 5</li> </ul>
6/3/2014	<ul style="list-style-type: none"> <li>• Updated IC @ TC 25C from "40A" to "60A" on page 1, 2</li> <li>• Updated schematic on page 1</li> <li>• Updated fig 8 and 9 on page 4</li> <li>• Updated fig14 on page 5</li> <li>• Updated Tape and Reel on page 8</li> </ul>
12/09/2014	<ul style="list-style-type: none"> <li>• Updated <math>R_{DS(on)}</math> from 2.2mΩ to 2.4mΩ in accordance with PCN#188, For backwards compatibility, datasheet thermal calculations remain unchanged (<math>R_{DS(on)} = 2.2\text{ m}\Omega</math>)</li> </ul>
2/26/2016	<ul style="list-style-type: none"> <li>• Updated datasheet with corporate template</li> <li>• Removed package outline "Punched Version" on page 7.</li> </ul>

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